

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

32,768 WORDS $\times$ 8 BIT STATIC RAM

DESCRIPTION

The TC55257DPI is 262,144 bit static random access memory organized as 32,768 words by 8 bits using CMOS technology, and operated from a single 2.7~5.5V supply. Advanced circuit techniques provide both high speed and low power features with an operating current of 5 mA / MHz (Typ.) and minimum cycle time of 70 ns.

When CE is a logical high, the device is placed in low power standby mode in which standby current is 0.3 μ A typically. The TC55257DPI has two control inputs. Chip enable (CE) allows for device selection and data retention control, and an output enable input (OE) provides fast memory access. Thus the TC55257DPI is suitable for use in various microprocessor application systems where high speed, low power, and battery back up are required. And TC55257DPI guarantees -40~85°C operating temperature, so TC55257DPI is suitable for use in wide operating temperature system.

The TC55257DPI is offered in a standard dual-in-line 28 pin plastic package (0.6 inch width), small-out-line plastic package and thin-small-out-line plastic package (forward type, reverse type).

FEATURES

- Low Power Dissipation
27.5 mW / MHz (Typ.) Operating
- Standby Current : 2 μ A (Max.) at Ta = 25°C
- Single Power Supply : 2.7~5.5 V
- Power Down Feature : CE
- Data retention Supply Voltage : 2.0~5.5 V
- Directly TTL Compatible
: All Inputs and Outputs
- Wide Temperature Operating : -40~85°C

- Access Time (Max.) :

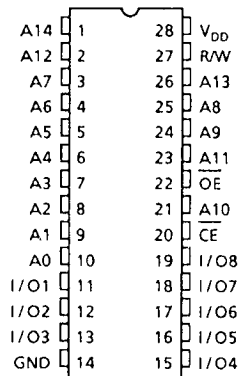
	5V $\pm$ 10%		2.7~5.5V	
	-70V	-85V	-70V	-85V
Access Time	70ns	85ns	120ns	150ns
CE Access Time	70ns	85ns	120ns	150ns
OE Access Time	35ns	45ns	70ns	75ns

- Package :

DIP28-P-600-2.54 (DPI) (Weight: 4.42 g typ)
 SOP28-P-450-1.27 (DFI) (Weight: 0.79 g typ)
 TSOP I 28-P-0.55 (DFTI) (Weight: 0.22 g typ)
 TSOP I 28-P-0.55A (DTRI) (Weight: 0.22 g typ)

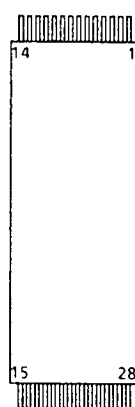
PIN CONNECTION (TOP VIEW)

o 28 PIN DIP & SOP



o 28 PIN TSOP

(forward type)



(reverse type)



PIN NAME

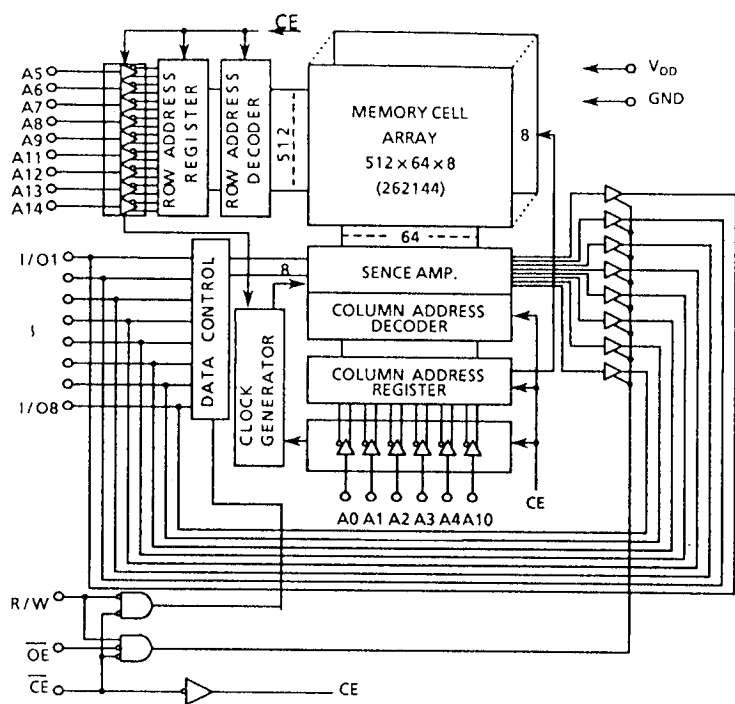
A0~A14	Address Inputs
R/W	Read / Write Control Input
OE	Output Enable Input
CE	Chip Enable Input
I/O1~I/O8	Data Input / Output
V _{DD}	Power
GND	Ground

PIN NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
PIN NAME	OE	A ₁₁	A ₉	A ₈	A ₁₃	R/W	V _{DD}	A ₁₄	A ₁₂	A ₇	A ₆	A ₅	A ₄	A ₃
PIN NO.	15	16	17	18	19	20	21	22	23	24	25	26	27	28
PIN NAME	A ₂	A ₁	A ₀	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	CE	A ₁₀

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BLOCK DIAGRAM



OPERATION MODE

OPERATION MODE	$\overline{CE}$	$\overline{OE}$	R/W	I/O1~I/O8	POWER
Read	L	L	H	D _{OUT}	I _{DDO}
Write	L	*	L	D _{IN}	I _{DDO}
Output Deselect	L	H	H	High-Z	I _{DDO}
Standby	H	*	*	High-Z	I _{DDs}

* : H or L

ABSOLUTE MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT
V _{DD}	Power Supply Voltage	-0.3~7.0	V
V _{IN}	Input Voltage	-0.3*~7.0	V
V _{I/O}	Input and Output Voltage	-0.5*~V _{DD} +0.5	V
P _D	Power Dissipation	1.0/0.6**	W
T _{solder}	Soldering Temperature (10s)	260	°C
T _{strg}	Storage Temperature	-55~150	°C
T _{opr}	Operating Temperature	-40~85	°C

* : -3.0 V at pulse width 50 ns

** : SOP

D.C. RECOMMENDED OPERATING CONDITIONS ($T_a = -40 \sim 85^\circ\text{C}$)

SYMBOL	PARAMETER	5V $\pm$ 10%			2.7~5.5V			UNIT
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V_{DD}	Power Supply Voltage	4.5	—	5.5	2.7	—	5.5	V
V_{IH}	Input High Voltage	2.4	—	$V_{DD} + 0.3$	$V_{DD} - 0.2$	—	$V_{DD} + 0.3$	
V_{IL}	Input Low Voltage	-0.3*	—	0.6	-0.3*	—	0.2	
V_{DH}	Data Retention Supply Voltage	2.0	—	5.5	2.0	—	5.5	

*: -3.0V at pulse width at 50ns Max.

D.C. and OPERATING CHARACTERISTICS ($T_a = -40 \sim 85^\circ\text{C}$, $V_{DD} = 5\text{V} \pm 10\%$)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
I_{IL}	Input Leakage Current	$V_{IN} = 0 \sim V_{DD}$	—	—	± 1.0	μA
I_{OH}	Output High Current	$V_{OH} = 2.4\text{V}$	-1.0	—	—	mA
I_{OL}	Output Low Current	$V_{OL} = 0.4\text{V}$	4.0	—	—	mA
I_{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or $R/W = V_{IL}$ or $\overline{OE} = V_{IH}$, $V_{OUT} = 0 \sim V_{DD}$	—	—	± 1.0	μA
I_{DDO1}	Operating Current	$\overline{CE} = V_{IL}$ $R/W = V_{IH}$, $I_{OUT} = 0\text{mA}$ Other Input = V_{IH}/V_{IL}	$t_{\text{cycle}} = 1\mu\text{s}$	—	10	mA
			$t_{\text{cycle}} = \text{Min. cycle}$	—	—	
I_{DDO2}		$\overline{CE} = 0.2\text{V}$ $R/W = V_{DD} - 0.2\text{V}$, $I_{OUT} = 0\text{mA}$ Other Input = $V_{DD} - 0.2\text{V}/0.2\text{V}$	$t_{\text{cycle}} = 1\mu\text{s}$	—	5	mA
			$t_{\text{cycle}} = \text{Min. cycle}$	—	—	
I_{DDs1}	Standby Current	$\overline{CE} = V_{IH}$	—	—	—	mA
I_{DDs2}		$\overline{CE} = V_{DD} - 0.2$ $V_{DD} = 2.0\text{V} \sim 5.5\text{V}$	$T_a = -40 \sim 85^\circ\text{C}$	—	—	30
			$T_a = 25^\circ\text{C}$	—	0.3	2

D.C. and OPERATING CHARACTERISTICS (Ta = -40~85°C, V_{DD} = 3V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION			MIN.	TYP.	MAX.	UNIT
I _{IL}	Input Leakage Current	V _{IN} = 0 ~ V _{DD}			—	—	± 1.0	μA
I _{OH}	Output High Current	V _{OH} = V _{DD} - 0.2V			- 0.1	—	—	mA
I _{OL}	Output Low Current	V _{OL} = 0.2V			0.1	—	—	mA
I _{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or R/W = V _{IL} or $\overline{OE} = V_{IH}$, V _{OUT} = 0 ~ V _{DD}			—	—	± 1.0	μA
I _{DDO2}	Operating Current	$\overline{CE} = 0.2V$ R/W = V _{DD} - 0.2V, I _{OUT} = 0mA Other Input = V _{DD} - 0.2V / 0.2V	T _{cycle}	Min.	—	—	20	mA
				1μs	—	—	5	
I _{DD52}	Standby Current	$\overline{CE} = V_{DD} - 0.2V$	V _{DD} = 3V ± 10%	Ta = 25°C	—	1	1.5	μA
				Ta = -40 ~ 85°C	—	—	20	
		V _{DD} = 3.0V		Ta = 25°C	—	—	1	
				Ta = -40 ~ 40°C	—	—	2	
				Ta = -40 ~ 85°C	—	—	15	

CAPACITANCE (Ta = 25°C, f = 1MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX.	UNIT
C _{IN}	Input Capacitance	V _{IN} = GND	10	pF
C _{OUT}	Output Capacitance	V _{OUT} = GND	10	pF

Note : This parameter periodically sampled is not 100% tested.

A.C. CHARACTERISTICS (Ta = -40~85 °C, VDD = 5 V ± 10%)

Read Cycle

SYMBOL	PARAMETER	TC55257DPI / DFI / DFTI / DTRI				UNIT
		- 70V		- 85V		
		MIN.	MAX.	MIN.	MAX.	
t _{RC}	Read Cycle Time	70	–	85	–	ns
t _{ACC}	Address Access Time	–	70	–	85	
t _{CO}	CE Access Time	–	70	–	85	
t _{OE}	Output Enable to Output in Valid	–	35	–	45	
t _{COE}	Chip Enable to Output in Low-Z	5	–	5	–	
t _{OEE}	Output Enable to Output in Low-Z	0	–	0	–	
t _{OD}	Chip Enable to Output in High-Z	–	25	–	30	
t _{ODO}	Output Enable to Output in High-Z	–	25	–	30	
t _{OH}	Output Data Hold Time	10	–	10	–	

Write Cycle

SYMBOL	PARAMETER	TC55257DPI / DFI / DFTI / DTRI				UNIT
		- 70V		- 85V		
		MIN.	MAX.	MIN.	MAX.	
t _{WC}	Write Cycle Time	70	–	85	–	ns
t _{WP}	Write Pulse Width	50	–	60	–	
t _{CW}	Chip Selection to End of Write	60	–	65	–	
t _{AS}	Address Set up Time	0	–	0	–	
t _{WR}	Write Recovery Time	0	–	0	–	
t _{ODW}	R / W to Output in High-Z	–	25	–	30	
t _{OEW}	R / W to Output in Low-Z	0	–	0	–	
t _{DS}	Data Set up Time	30	–	40	–	
t _{DH}	Data Hold Time	0	–	0	–	

A.C. Test Conditions

Output Load : 100 pF + 1 TTL Gate (-70V, -85V)
 Input Pulse Level : 0.4 V, 2.6 V
 Timing Measurement : 1.5 V
 Reference Level : 1.5 V
 t_r, t_f : 5 ns

A.C. CHARACTERISTICS ($T_a = -40 \sim 85^\circ\text{C}$, $V_{DD} = 2.7 \sim 5.5\text{V}$)

Read Cycle

SYMBOL	PARAMETER	TC55257DPI / DFI / DFTI / DTRI				UNIT
		– 70V		– 85V		
		MIN.	MAX.	MIN.	MAX.	
t _{RC}	Read Cycle Time	120	–	150	–	ns
t _{ACC}	Address Access Time	–	120	–	150	
t _{CO}	$\overline{CE}$ Access Time	–	120	–	150	
t _{OE}	Output Enable to Output in Valid	–	70	–	75	
t _{COE}	Chip Enable to Output in Low-Z	5	–	5	–	
t _{OEE}	Output Enable to Output in Low-Z	0	–	0	–	
t _{OD}	Chip Enable to Output in High-Z	–	50	–	50	
t _{ODO}	Output Enable to Output in High-Z	–	50	–	50	
t _{OH}	Output Data Hold Time	10	–	10	–	

Write Cycle

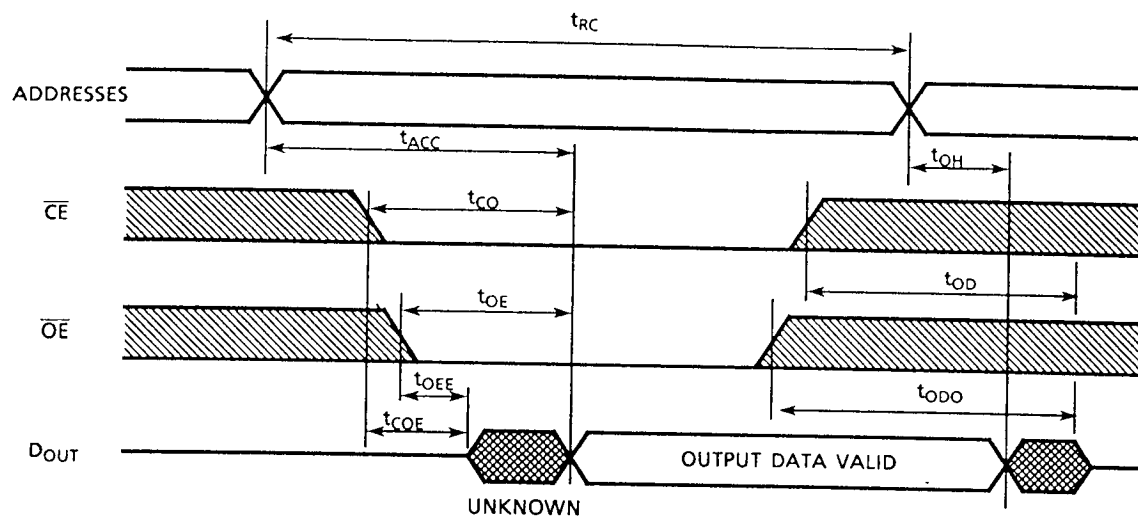
SYMBOL	PARAMETER	TC55257DPI / DFI / DFTI / DTRI				UNIT
		– 70V		– 85V		
		MIN.	MAX.	MIN.	MAX.	
t _{WC}	Write Cycle Time	120	–	150	–	ns
t _{WP}	Write Pulse Width	80	–	100	–	
t _{CW}	Chip Selection to End of Write	100	–	120	–	
t _{AS}	Address Set up Time	0	–	0	–	
t _{WR}	Write Recovery Time	0	–	0	–	
t _{ODW}	R/W to Output in High-Z	–	50	–	50	
t _{OEW}	R/W to Output in Low-Z	0	–	0	–	
t _{DS}	Data Set up Time	50	–	60	–	
t _{DH}	Data Hold Time	0	–	0	–	

A.C. TEST CONDITIONS

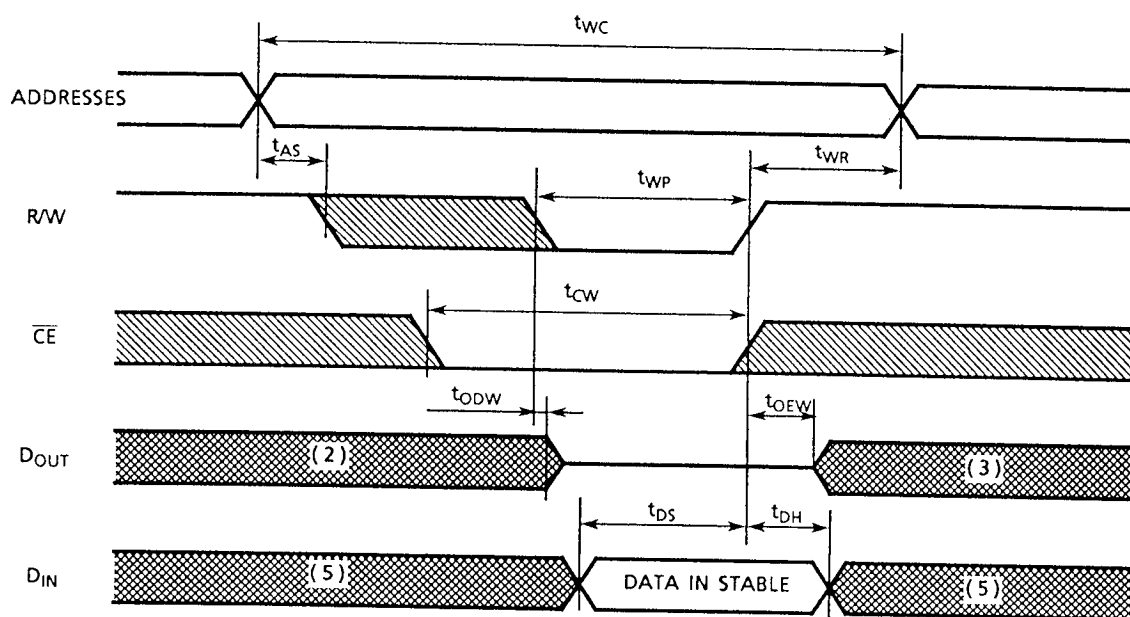
- Output Load : 100pF (Include Jig)
- Input Pulse Level : $V_{DD} - 0.2\text{V} / 0.2\text{V}$
- Timing Measurement V_{IN} : 1.5V
Reference Level V_{OUT} : 1.5V
- t_r, t_f : 5ns

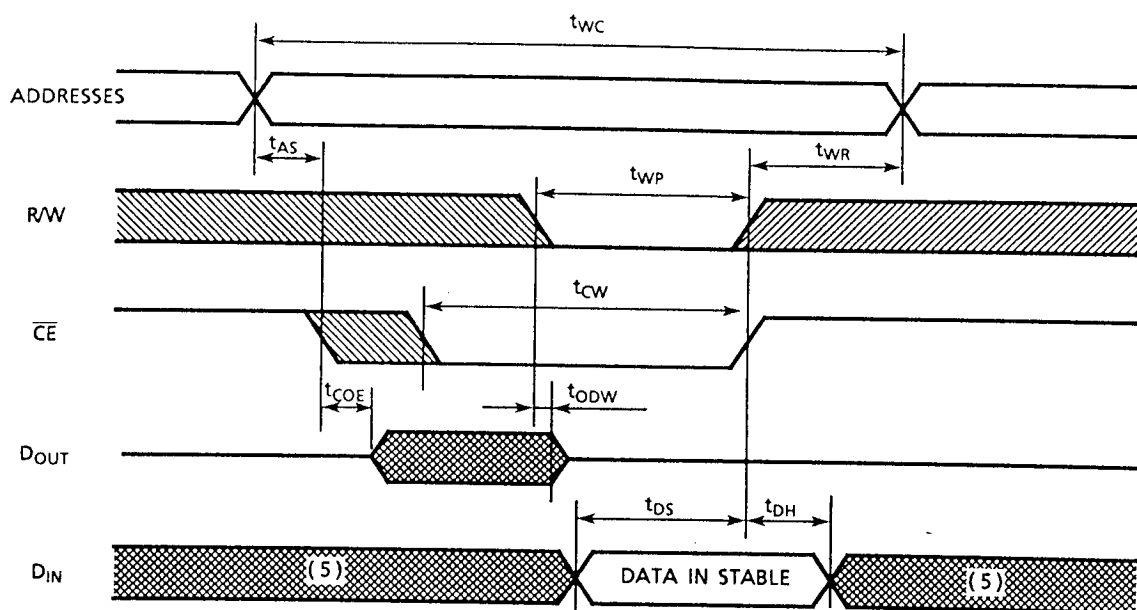
TIMING WAVEFORMS

Read Cycle (1)



Write Cycle 1 (4) (R/W Controlled Write)



Write Cycle 2 (4) ($\overline{CE}$ Controlled Write)


Note : (1) R/W is High for read cycle.

- (2) Assuming that $\overline{CE}$ low transition occurs coincident with or after R / W Low transition, Outputs remain a high impedance state.
- (3) Assuming that $\overline{CE}$ High transition occurs coincident with or prior to R / W High transition, Outputs remain a high impedance state.
- (4) Assuming that $\overline{OE}$ is High for Write Cycle, Outputs are in high impedance state during this period.
- (5) The I/O may be in the output state at this time, input signals of opposite phase must not be applied.

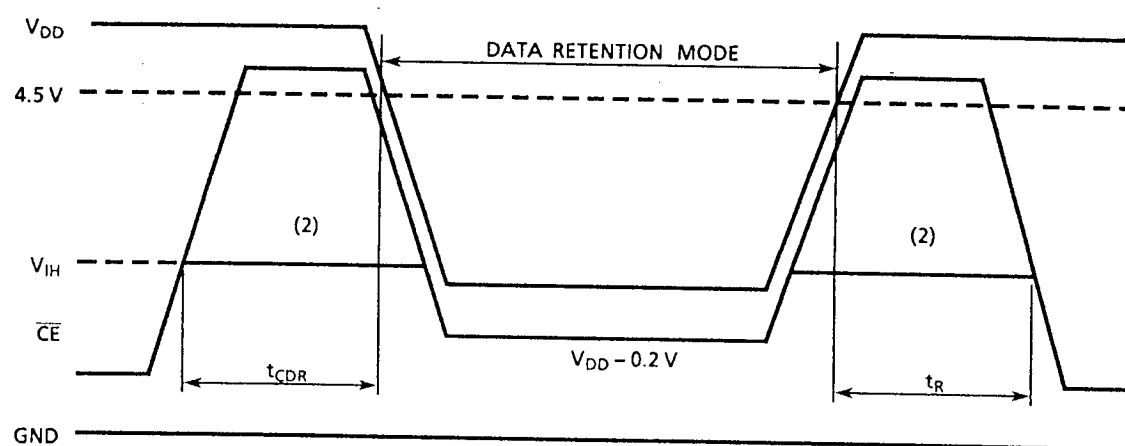
DATA RETENTION CHARACTERISTICS (Ta = -40~85 °C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{DH}	Data Retention Supply Voltage	2.0	—	5.5	V
I_{DD52}	Standby Supply Current	$V_{DH} = 3.0\text{ V}$	—	15*	μA
		$V_{DH} = 5.5\text{ V}$	—	30	μA
t_{CDR}	Chip Deselection to Data Retention Mode		—	—	ns
t_R	Recovery Time		—	—	ns

Note (1) : Read Cycle Time.

*) 2 μA (Max.) Ta = -40~40°C

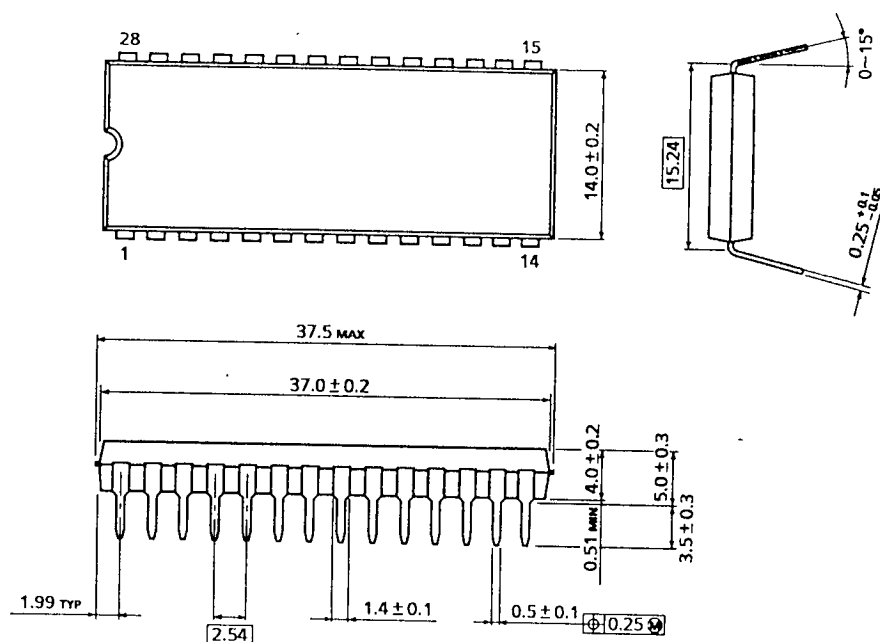
$\overline{\text{CE}}$ Controlled Data Retention Mode



Note (2) : If the V_{IH} of $\overline{\text{CE}}$ is 2.4 V in operation, I_{DD51} current flows during the period that the V_{DD} voltage is going down from 4.5 V to 2.6 V

PACKAGE DIMENSIONS (DIP28-P-600-2.54)

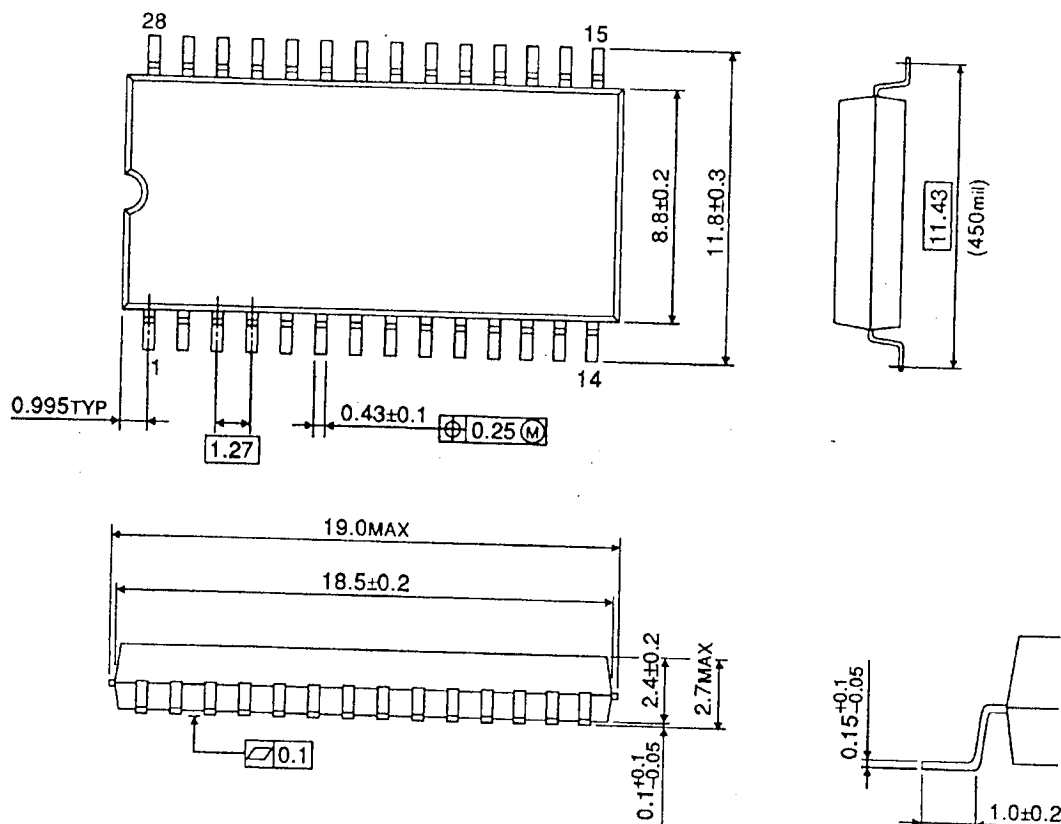
Units in mm



Weight: 4.42 g (typ)

PACKAGE DIMENSIONS (SOP28-P-450-1.27)

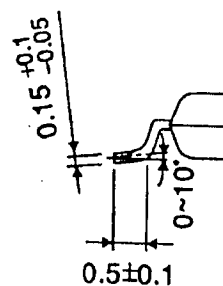
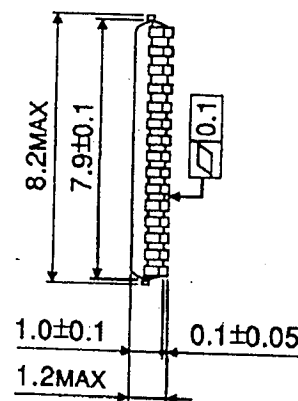
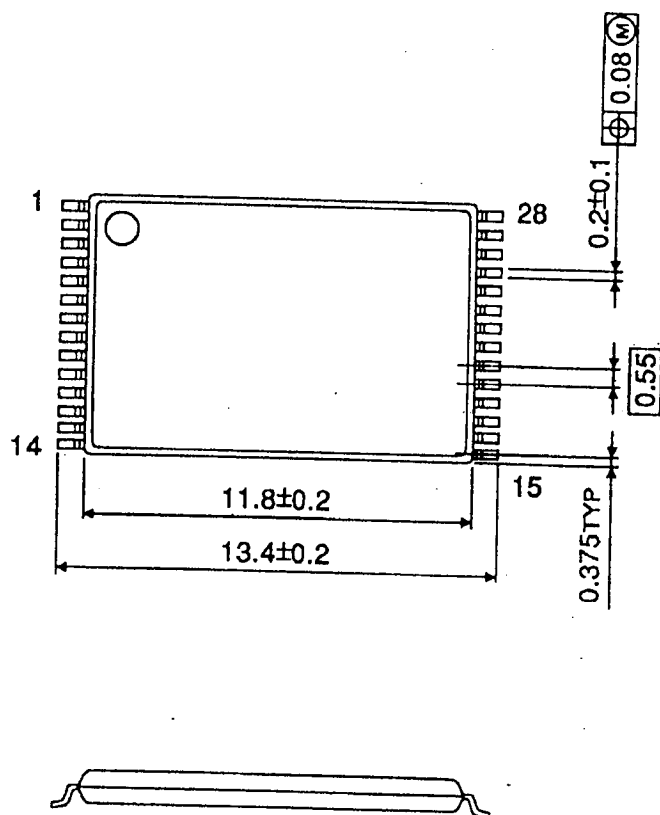
Units in mm



Weight: 0.79 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55)

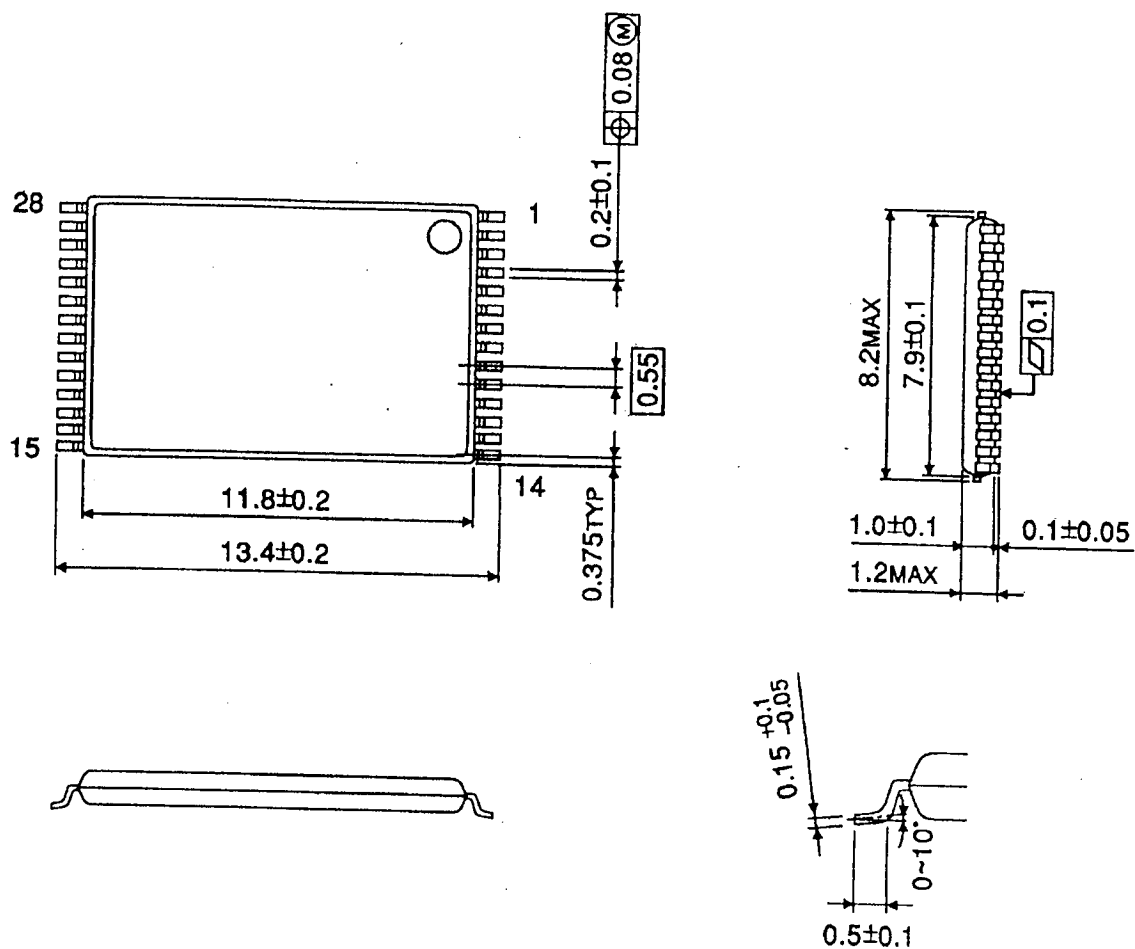
Units in mm



Weight: 0.22 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55A)

Units in mm



Weight: 0.22 g (typ)